V_{DSS}	800 V
I_D	8.5 A
$R_{DS(ON)}$	280 mΩ

FEATURES

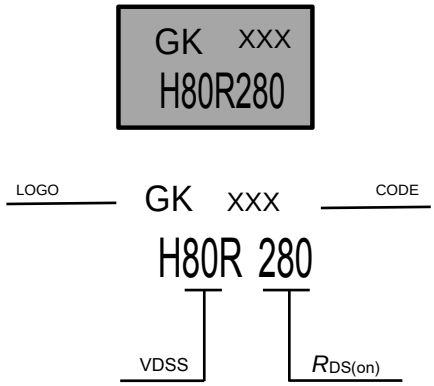
- Wide Bandgap SiC MOSFET Technology
- Low On-Resistance with High Blocking Voltage
- Low Capacitances with High-Speed Switching
- Low Reverse Recovery (Qrr)
- Easy to Parallel and Simple to Drive

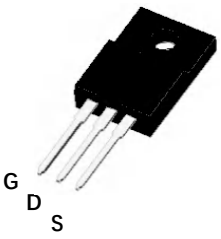
BENEFITS

- Reduced Switching Losses
- Increased System Switching Frequency
- Increased Power Density
- Reduction of Heat Sink Requirements
- Reduced EMI

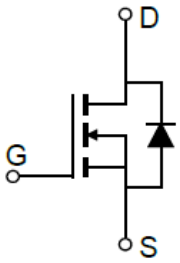
APPLICATION

- Switch Mode Power Supplies
- High Voltage DC/DC Converters
- Battery Chargers
- Motor Drives
- Pulsed Power Applications





ITO-220AB TopView



Schematic Diagram

ABSOLUTE MAXIMUM RATINGS (T_C = 25°C, unless otherwise specified)

Parameter	Symbol	Test Condition	Value	Unit
Drain to Source Voltage	V_{DS}	V_{GS} = 0V	800	V
Gate to Source Voltage	V_{GS}	Absolute maximum values	-10/+22	V
Recommended Operation Voltage of Gate to Source	V_{GSop}	Recommended operational values	0/+18	V
Continuous Drain Current	I_D	V_{GS}=18V, T_C=25℃	8.5	A
		V_{GS}=18V, T_C=100℃	6.0	
Pulsed Drain Current	I_{DM}	V_{GS}=18V, T_C=25℃	17.0	A
Power Dissipation	P_{tot}	T_C=25℃, T_j=175℃	26.8	W
Operating and Storage Temperature	T_j, T_{stg}		-55 to +175	℃

ELECTRICAL CHARACTERISTICS (T_C=25°C, unless otherwise specified)

Static Characteristics

Parameter	Symbol	Test Condition	Value			Unit
			Min.	Typ.	Max.	
Drain to Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS}=0V, I_D=500μA	800			V
Gate Threshold Voltage	$V_{GS(th)}$	V_{GS}= V_{DS}, I_D=1.8mA	2.6		4.6	V
Zero Gate Voltage Drain Current	I_{DSS}	V_{GS}=0V, V_{DS}=800V, T_j=25℃			100	μA
Gate to Source Leakage Current	I_{GSS}	V_{GS}=18V, V_{DS}=0V			250	nA
Drain to Source on Resistance	$R_{DS(on)}$	V_{GS}=15V, I_D=5A		415		mΩ
		V_{GS}=15V, I_D=5A, T_j=175℃		340		
		V_{GS}=18V, I_D=5A		280	364	
		V_{GS}=18V, I_D=5A, T_j=175℃		276		

Dynamic Characteristics

Parameter	Symbol	Test Condition	Value			Unit
			Min.	Typ.	Max.	
Input Capacitance	C_{iss}	V_{GS}=0V, V_{DS}=400V, f=100KHz, T_j=25℃		267		pF
Output Capacitance	C_{oss}			21.1		
Reverse Transfer Capacitance	C_{rss}			2.21		
Total Gate Charge	Q_g	V_{GS}=0/18V, V_{DS}=400V, I_D=5A, T_j=25℃		22.3		nC
Gate-Source Charge	Q_{gs}			10.3		
Gate-Drain Charge	Q_{gd}			5.9		
Gate Resistance	R_g	f=1MHz		6.4		Ω

Thermal Characteristics

Parameter	Symbol	Value			Unit
		Min.	Typ.	Max.	
Thermal Resistance from Junction to Case	$R_{th(j-c)}$	-	5.6	-	℃/W

ELECTRICAL CHARACTERISTICS (T_C=25°C, unless otherwise specified)

Switching Characteristics

Parameter	Symbol	Test Condition	Value			Unit
			Min.	Typ.	Max.	
Turn-On Delay Time	$t_{d(on)}$	V_{GS}=0/18V, V_{DD}=400V, I_D=5A, R_g=5Ω, L=200uH		12.0		ns
Rise Time	t_r			40.4		
Turn-Off Delay Time	$t_{d(off)}$			16.0		
Fall Time	t_f			39.2		

Reverse Diode Characteristics

Parameter	Symbol	Test Condition	Value			Unit
			Min.	Typ.	Max.	
Diode Forward Voltage	V_{SD}	V_{GS}=0V, I_{SD}=3A, T_j=25℃	-	3.5		V
Continuous Diode Forward Current	I_S	V_{GS}=0V, T_j=25℃		8.5		A
Reverse Recovery Time	t_{rr}	V_{GS} = 0V, I_{SD}=5A, V_R=400V, di/dt=830A/us, T_j=25℃		11.2		ns
Reverse Recovery Charge	Q_{rr}			31.8		nC
Peak Reverse Recovery Current	I_{rrm}			4.8		A

RATING AND CHARACTERISTIC CURVES

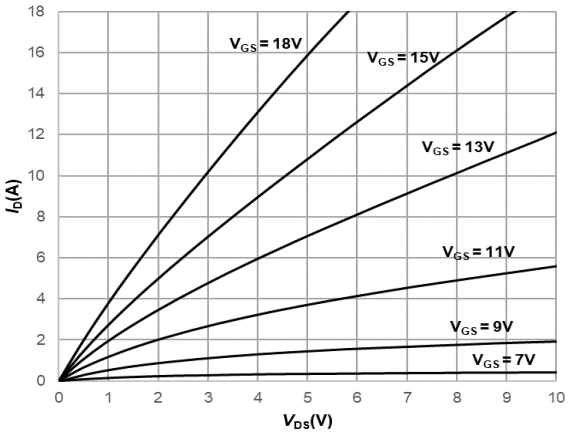


Fig1. Output Characteristics T_j=25℃

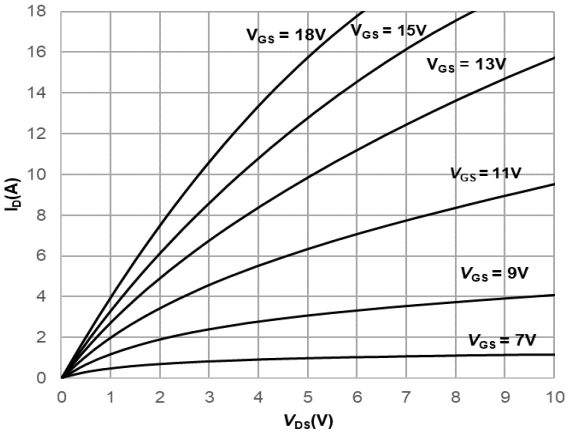


Fig2. Output Characteristics T_j=175℃

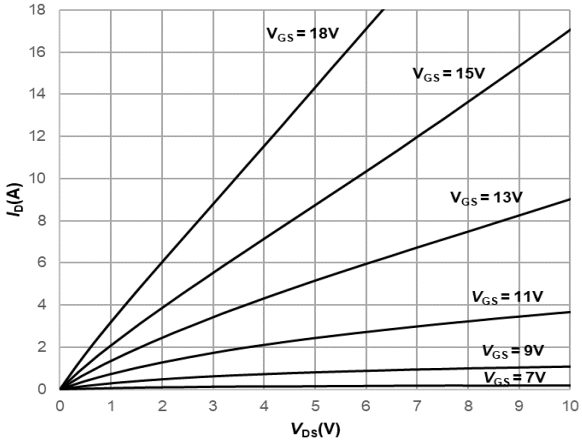


Fig3. Output Characteristics T_j= -40℃

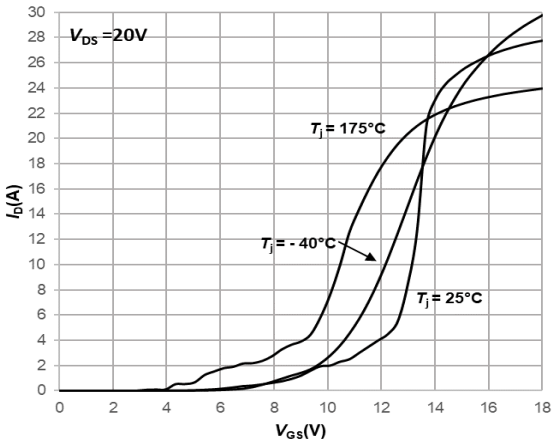


Fig4. Typical Transfer Characteristics

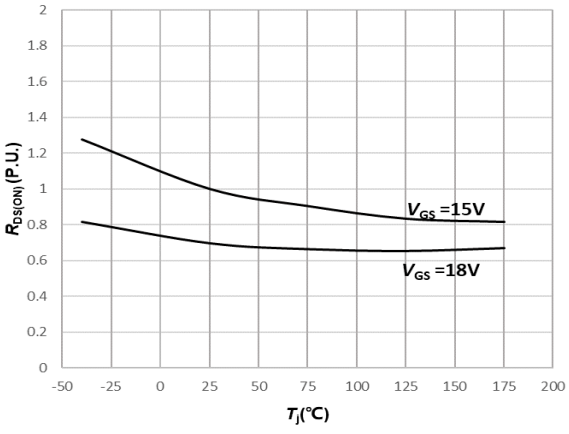


Fig5. Normalized On-Resistance vs. Temperature

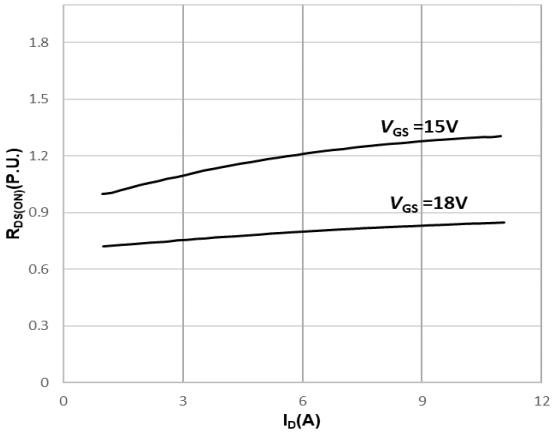


Fig6. Normalized On-Resistance vs. Drain Current For T_j=25℃

RATING AND CHARACTERISTIC CURVES

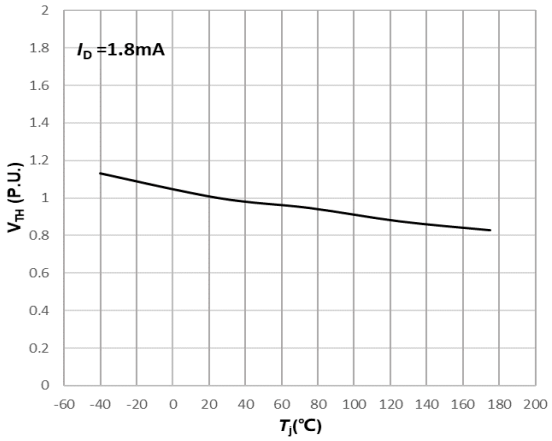


Fig7. Normalized Threshold Voltage vs. Temperature

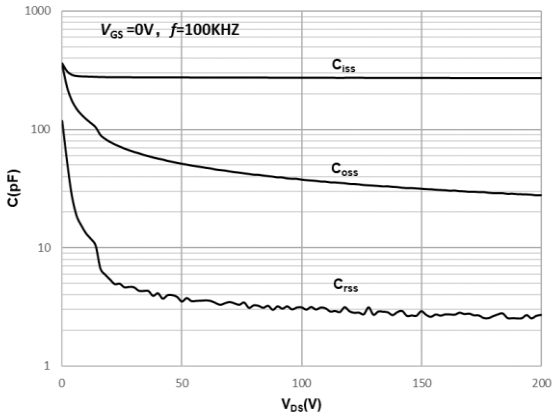


Fig8. Capacitances vs. Drain-Source Voltage (0-200V)

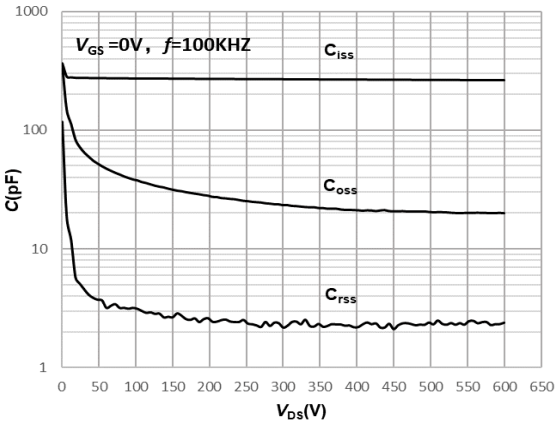


Fig9. Capacitances vs. Drain-Source Voltage (0-600V)

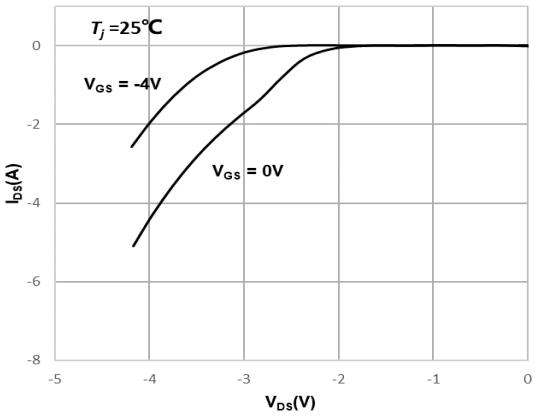


Fig10. Body Diode Characteristics

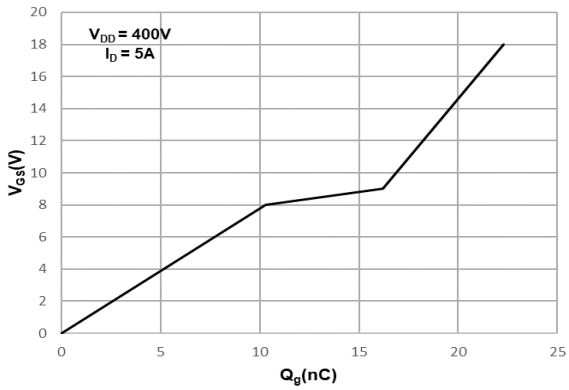


Fig11. Gate Charge Characteristic

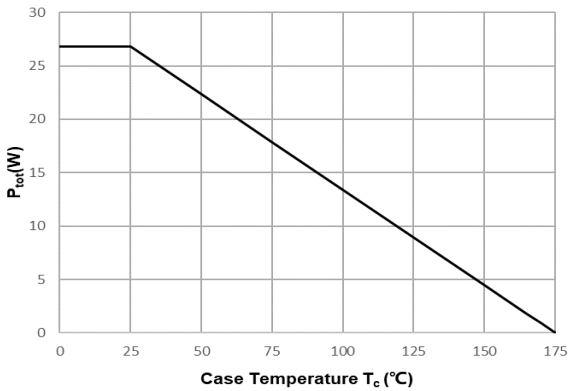


Fig12. Power Dissipation vs. Case temperature

RATING AND CHARACTERISTIC CURVES

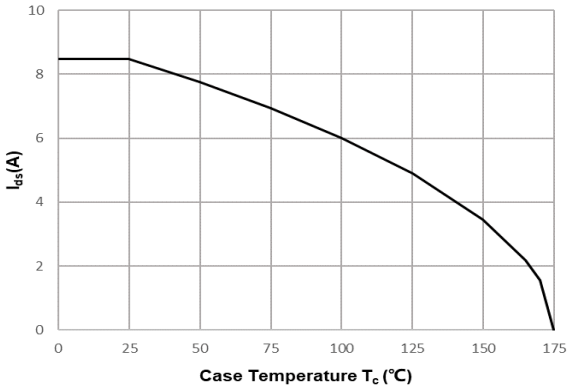
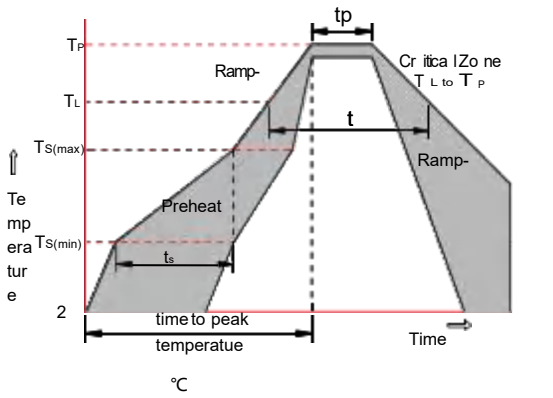


Fig13. Continuous Drain Current vs. Case Temperature

Soldering parameters

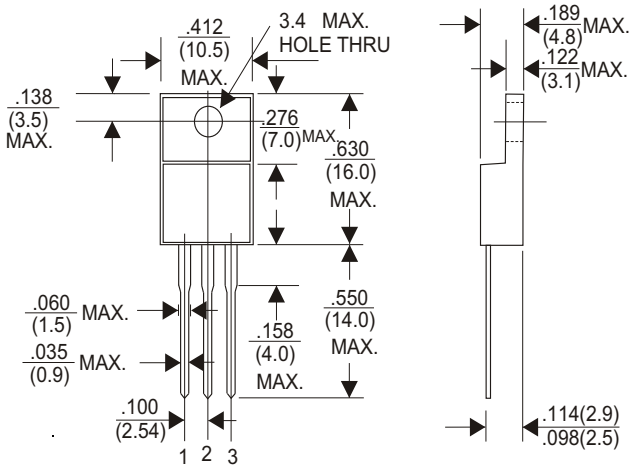
Reflow Condition		Pb-Free assembly (see as bellow)
Pre Heat	-Temperature Min ($T_{s(min)}$)	+150℃
	-Temperature Max($T_{s(max)}$)	+200℃
	-Time (Min to Max) (ts)	60-180 secs.
Average ramp up rate (Liquid us Temp (T_L) to peak)		3℃/sec. Max
$T_{s(max)}$ to T_L - Ramp-up Rate		3℃/sec. Max
Reflow	-Temperature(T_L)(Liquid us)	+217℃
	-Temperature(t_L)	60-150 secs.
Peak Temp (T_p)		+260(+0/-5)℃
Time within 5℃ of actual Peak Temp (t_p)		30 secs. Max
Ramp-down Rate		6℃/sec. Max
Time 25℃ to Peak Temp (T_P)		8 min. Max
Do not exceed		+260℃

FIG5: Reflow condition



Package Dimensions & Suggested Pad Layout

ITO-220AB **(FULLYINSULATED)**



Dimensions in inches and (millimeters)